

Appl. No. 09/653,157

version, except that marked up versions are not being supplied for any added claim or canceled claim.

A¹ Sub 1
1. (Amended) A method of removing at least some of a material from a semiconductor substrate, comprising:

feeding a single feed gas through an ozone generator to generate ozone from the feed gas; the feed gas comprising at least 99.999% O₂ (by volume); and

contacting the ozone or a fragment of the ozone with a material on a semiconductor substrate to remove at least some of the material from the semiconductor substrate.

A² Sub 2
7. (Amended) A method of removing at least some of a material from a semiconductor substrate, comprising:

feeding a single feed gas through an ozone generator to generate ozone from the feed gas; the feed gas comprising O₂ and less than or equal to 0.001% N₂ (by volume); and

contacting the ozone or a fragment of the ozone with a material on a semiconductor substrate to remove at least some of the material from the semiconductor substrate.